

Abstracts

Two-Dimensional Transmission Line Matrix (TLM) Simulation of the Electromagnetic Fields in a Rectangular Section of a Discretized GaAs MESFET Channel with Arbitrary Doping Profile

S. Dindo and M. Ney. "Two-Dimensional Transmission Line Matrix (TLM) Simulation of the Electromagnetic Fields in a Rectangular Section of a Discretized GaAs MESFET Channel with Arbitrary Doping Profile." 1993 MTT-S International Microwave Symposium Digest 93.3 (1993 Vol. III [MWSYM]): 1455-1458.

A two-dimensional lossy shunt TLM network is adapted to simulate the Maxwell field equations of a GaAs MESFET. By discretizing the channel into rectangular sections of single thickness, the new TLM technique is shown, with examples, that it can simulate the calculated electromagnetic fields of an arbitrarily doped channel section.

[Return to main document.](#)